Optical Component Product News

807nm 40W LD bar

ML5CP8

new

Features

- Bare 10mm x 1.0mm laser diode bar
- High Output Power: 40 W (CW)
- Highly reliable active layer :
  Al-free MOCVD structure
- Lasing Wavelength: 807 nm (typ.)
- Good suitability for hard solder bonding as AuSn
- Fill Factor: 40%

Applications

- Nd:YAG Laser Pumping
- Direct-Use Applications

Description

ML5CP8 is a high-power, high-efficient semiconductor laser bar which provides a stable oscillation with emission wavelength of 807nm and standard CW light output of 40W.
ML5CP8 has small internal loss which improves the slope efficiency (reduction of the operating current).
Also, ML5CP8 has an Al-free single quantum well active layer, which prevents Catastrophic Optical Degradation (COD) even at extremely high output powers. That leads to highly reliable operation.

Structure

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